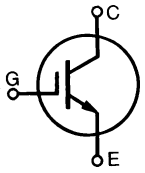
IXYS

Preliminary Data Sheet

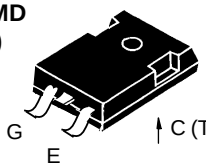
HiPerFAST™ IGBT

IXGH32N50B
IXGH32N50BS

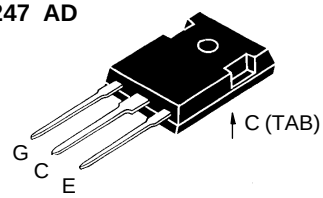
V_{CES} = 500 V
I_{C25} = 60 A
$V_{CE(sat)}$ = 2.0 V
t_{fi} = 80 ns



TO-247 SMD (32N50BS)



TO-247 AD



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C	500	V
V_{CGR}	T_J = 25°C to 150°C; R_{GE} = 1 MΩ	500	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C	60	A
I_{C90}	T_C = 90°C	32	A
I_{CM}	T_C = 25°C, 1 ms	120	A
SSOA (RBSOA)	V_{GE} = 15 V, T_{VJ} = 125°C, R_G = 33 Ω Clamped inductive load, L = 100 µH	I_{CM} = 64 @ 0.8 V_{CES}	A
P_C	T_C = 25°C	200	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	°C
M_d	Mounting torque (M3)	1.13/10	Nm/lb.in.
Weight	TO-247 AD	6	g
	TO-247 SMD	4	g

Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
BV_{CES}	I_C = 250 µA, V_{GE} = 0 V		500			V
$V_{GE(th)}$	I_C = 250 µA, V_{CE} = V_{GE}		2.5		5	V
I_{CES}	V_{CE} = 0.8 • V_{CES}	T_J = 25°C			200	µA
	V_{GE} = 0 V	T_J = 125°C			1	mA
I_{GES}	V_{CE} = 0 V, V_{GE} = ±20 V				±100	nA
$V_{CE(sat)}$	I_C = I_{C90}, V_{GE} = 15 V				2.0	V

Features

- International standard packages JEDEC TO-247 SMD surface mountable and JEDEC TO-247 AD
- High current handling capability
- Newest generation HDMOS™ process
- MOS Gate turn-on
  - drive simplicity

Applications

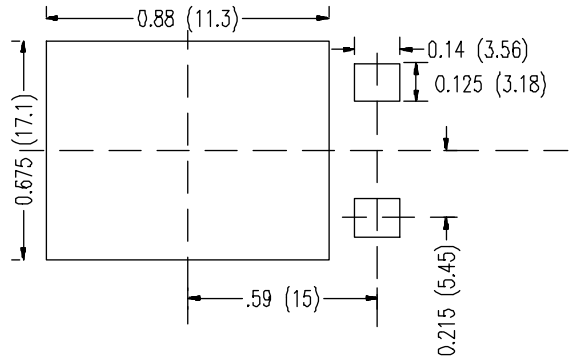
- PFC circuits
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies

Advantages

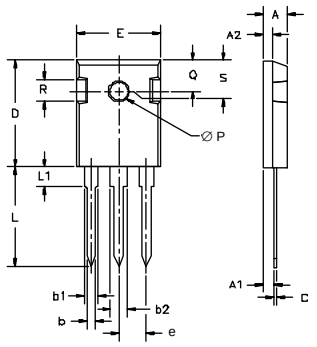
- High power density
- Very fast switching speeds for high frequency applications

Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)	Characteristic Values min.	typ.	max.	
g_{fs}	$I_C = I_{C90}$; V_{CE} = 10 V, Pulse test, t ≤ 300 µs, duty cycle ≤ 2 %	15	20		S
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		2500		pF
C_{oes}			230		pF
C_{res}			70		pF
Q_g	$I_C = I_{C90}$, V_{GE} = 15 V, V_{CE} = 0.5 V_{CES}		125	150	nC
Q_{ge}			23	35	nC
Q_{gc}			50	75	nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**		25		ns
t_{ri}	$I_C = I_{C90}$, V_{GE} = 15 V, L = 100 µH,		30		ns
$t_{d(off)}$	V_{CE} = 0.8 V_{CES}, $R_G = R_{off}$ = 4.7 Ω		100	200	ns
t_{fi}	Remarks: Switching times may		80	150	ns
E_{off}	increase for V_{CE} (Clamp) > 0.8 • V_{CES}, higher T_J or increased R_G		0.7	1.5	mJ
$t_{d(on)}$	**Inductive load, T_J = 125°C**		25		ns
t_{ri}	$I_C = I_{C90}$, V_{GE} = 15 V, L = 100 µH		35		ns
E_{on}	V_{CE} = 0.8 V_{CES}, $R_G = R_{off}$ = 4.7 Ω		0.3		mJ
$t_{d(off)}$	Remarks: Switching times may		120		ns
t_{fi}	increase for V_{CE} (Clamp) > 0.8 • V_{CES},		120		ns
E_{off}	higher T_J or increased R_G		1.2		mJ
R_{thJC}				0.62	K/W
R_{thCK}			0.25		K/W

Min. Recommended Footprint (Dimensions in inches and (mm))

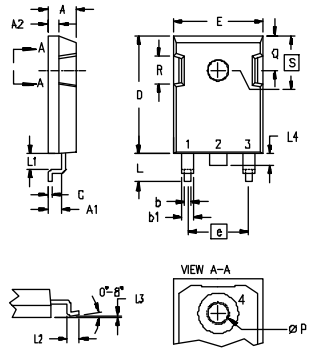


TO-247 AD Outline



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.7	5.3	.185	.209
A_1	2.2	2.54	.087	.102
A_2	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b_1	1.65	2.13	.065	.084
b_2	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

TO-247 SMD Outline



1. Gate
2. Collector
3. Emitter
4. Collector

Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.83	5.21	.190	.205
A1	2.29	2.54	.090	.100
A2	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b1	1.91	2.13	.075	.084
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45	BSC	.215	BSC
L	4.90	5.10	.193	.201
L1	2.70	2.90	.106	.114
L2	2.10	2.30	.083	.091
L3	0.00	0.10	.00	.004
L4	1.90	2.10	.075	.083
ØP	3.55	3.65	.140	.144
Q	5.59	6.20	.220	.244
R	4.32	4.83	.170	.190
S	6.15	BSC	.242	BSC